

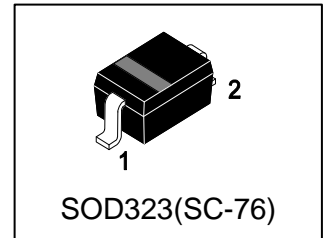
LBAS16HT1G

S-LBAS16HT1G

Switching Diode

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Small plastic SMD package
- Continuous reverse voltage: max. 75 V.
- High-speed switching in hybrid thick and thin-film circuits.



2. DEVICE MARKING AND ORDERING INFORMATION

| Device | Marking | Shipping |
|------------|---------|-----------------|
| LBAS16HT1G | A6 | 3000/Tape&Reel |
| LBAS16HT3G | A6 | 10000/Tape&Reel |

3. MAXIMUM RATINGS(Ta = 25°C)

| Parameter | Symbol | Limits | Unit |
|-------------------------------------|---------|--------|------|
| Non-Repetitive Peak Reverse Voltage | VRM | 100 | V |
| Repetitive Peak Reverse Voltage | VRRM | 100 | V |
| Working Peak Reverse Voltage | VRWM | | |
| DC Blocking Voltage | VR | | |
| RMS Reverse Voltage | VR(RMS) | 71 | V |
| Forward Continuous Current | IFM | 500 | mA |
| Average Rectified Output Current | IO | 250 | mA |
| Non-Repetitive Peak Forward Current | IFSM | | |
| t=1μs | | 4 | A |
| t=1s | | 1.5 | A |

4. THERMAL CHARACTERISTICS

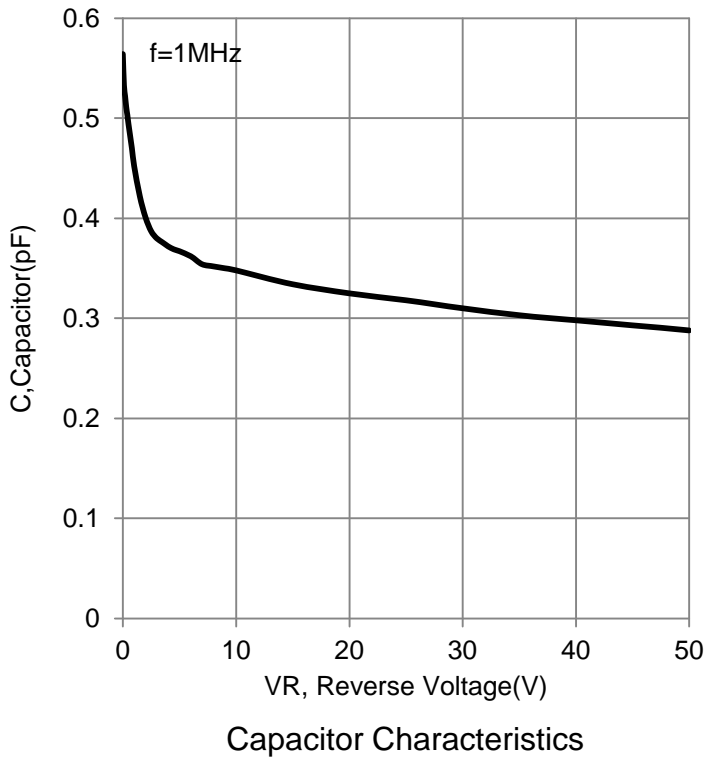
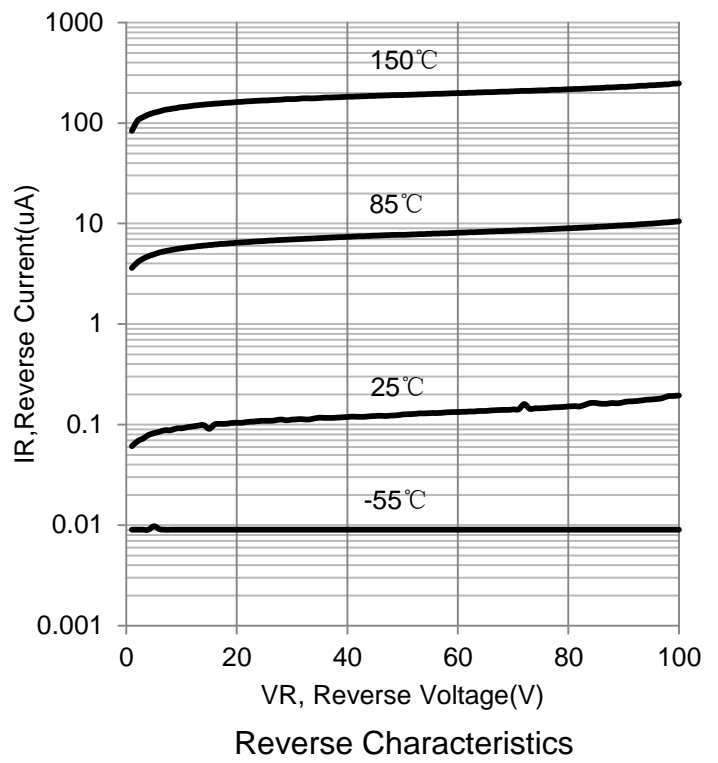
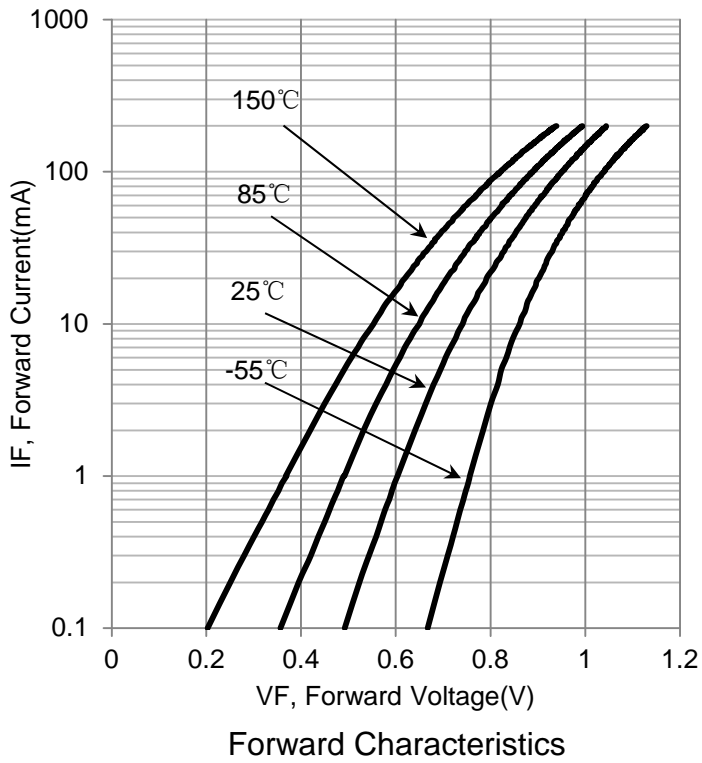
| Parameter | Symbol | Limits | Unit |
|---|---------|-------------|-------------|
| Total Device Dissipation, FR-5 Board (Note 1) @ TA = 25°C Derate above 25°C | PD | 200 1.57 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient(Note 1) | ROJA | 635 | °C/W |
| Junction and Storage temperature | TJ,Tstg | -55~+150 | °C |

1. FR-5 = 1.0×0.75×0.062 in.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

| Characteristic | Symbol | Min. | Typ. | Max. | Unit |
|--|--------|------|------|------|------|
| Reverse Breakdown Voltage (I(BR)=100μA) | VBR | 75 | - | - | V |
| Forward Voltage (IF = 1.0 mAdc) | VF | - | - | 715 | mV |
| (IF = 10 mAdc) | | - | - | 855 | |
| (IF = 50 mAdc) | | - | - | 1000 | |
| (IF = 150 mAdc) | | - | - | 1250 | |
| Reverse Voltage Leakage Current (VR = 75Vdc) | IR | - | - | 1.0 | μA |
| (VR = 75Vdc, TJ = 150°C) | | - | - | 50 | |
| (VR = 25Vdc, TJ = 150°C) | | - | - | 30 | |
| Diode Capacitance (VR = 0V, f = 1.0 MHz) | CD | - | - | 2.0 | pF |
| Reverse Recovery Time (IF=IR=10mAd,RL =50Ω) | trr | - | - | 4.0 | ns |
| Forward Recovery Voltage (IF = 10 mAdc, tr = 20 ns) | VFR | - | - | 1.75 | V |

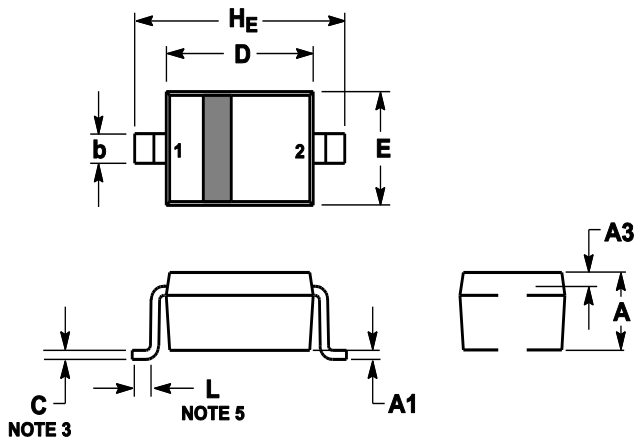
6. ELECTRICAL CHARACTERISTICS CURVES



7. OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|-------|----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.8 | 0.9 | 1 | 0.031 | 0.035 | 0.04 |
| A1 | 0 | 0.05 | 0.1 | 0 | 0.002 | 0.004 |
| A3 | 0.15REF | | | 0.006REF | | |
| b | 0.25 | 0.32 | 0.4 | 0.01 | 0.012 | 0.016 |
| C | 0.089 | 0.12 | 0.177 | 0.003 | 0.005 | 0.007 |
| D | 1.6 | 1.7 | 1.8 | 0.062 | 0.066 | 0.07 |
| E | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| L | 0.08 | | | 0.003 | | |
| HE | 2.3 | 2.5 | 2.7 | 0.09 | 0.098 | 0.105 |

8. SOLDERING FOOTPRINT

